

EAST - (10669216.write line with bias structure at ends.wsp:1)

File View Edit Tools Window Help

Drafts

- BRS:
- BRS:
- BRS:
- BRS: knall
- BRS: 19 21 23
- BRS: 32with 33

Pending

Active

- L1: (0) 10/669216
- L2: (0) "APPLIED SPINTRONICS".as.
- L3: (5) "TSANG, DAVID".in.
- L4: (168557) (ferr?electric ferr? adj electric ferr?magnetic ferr? adj magnetic FeRr
- L5: (20720) writ\$4 adj2 line
- L6: (789915) (hard) adj2 (layer magnetization) (high adj coor\$4) bias\$4
- L7: (113203) 6 near9 end
- L8: (184) 5 and 7
- L11: (2) 8 and 4
- L8: (7) 5 same 7
- L10: (44) 8 and 4

Failed

Saved

- (1) 08/948877
- (1738) "KONINKLIJKE PHILIPS".as.

Favorites

Tagged (3)

QB: USPAT:US PGPUB:EPO:JPO:DERWENT:IDM:TDO

Default operator: OR

Plurals

+highlight all hit terms initially

9 and 4

June 2004

	U	S	Investor	Document#	Page	P	Title	Current	Current	Current	Retrieval	S	C	P	Image	Doc	P
1			Gagl, Dietmar	US 2004008 20040:5			Method for operating an MRAM semiconduct	711/1								US 200400	
2			Amano, Mino	US 2003012 20030:1			Magnetic memory	365/173.365/171								US 200301	
3			Hidaka, Hidet	US 2004010 20040:2			Thin film magnetic memory device with mem	365/158								US 200401	
4			Hidaka, Hidet	US 2004009 20040:4			Thin film magnetic memory device for progra	365/232								US 200400	
5			Kai, Tadashi	US 2004006 20040:2			Magnetoresistive element and magnetic me	428/468/428/208								US 200400	
6			Hidaka, Hidet	US 2004008 20040:3			Thin film magnetic memory device having da	385/200								US 200400	
7			Tanizaki, Hir	US 2003022 20031:3			Thin film magnetic memory device having du	365/158								US 200302	
8			Luo, Jih-Shiu	US 2003021 20031:1			Nonvolatile memory device utilizing spin-valv	365/158								US 200302	
9			Iwata, Yoshih	US 2003016 20030:1			Magnetic random access memory	365/200								US 200301	
10			Neel, Gary T.	US 2003013 20030:2			Fluid dose, flow and coagulation sensor for m	73/53.0								US 200301	

Ready